

# isc N-Channel MOSFET Transistor

# **R6520KNZ**

### FEATURES

- Drain Current –I\_D= 20A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V<sub>DSS</sub>=650V(Min)
- Static Drain-Source On-Resistance
- :  $R_{DS(on)}$  = 205m  $\Omega$  (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRIPTION

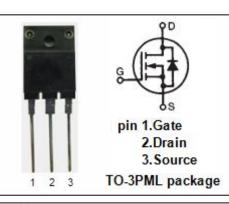
• Designed for use in switch mode power supplies and general purpose applications.

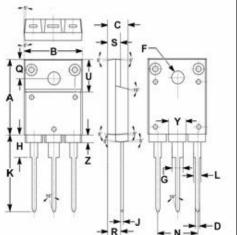
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	650	V			
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	V			
ID	Drain Current-Continuous	20	А			
I <sub>DM</sub>	Drain Current-Single Pluse	60	A			
PD	Total Dissipation @T <sub>c</sub> =25℃	68	W			
TJ	Max. Operating Junction Temperature	-55~150	°C			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.8	°C/W





	mm	
DIM	MIN	MAX
Α	19.90	20.10
В	15.75	16.10
С	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
Н	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
Ν	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

## isc website: <u>www.iscsemi.com</u>



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	650		V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =630uA	3	5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =9.5A		205	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0 V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0@T <sub>J</sub> =125°C		100 1000	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 20A; V <sub>GS</sub> = 0		1.5	V

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